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INTEGRATED CIRCUITS

DATA SHEET

GTL16612 18-bit GTL/GTL+ to LVTTL/TTL bidirectional universal translator (3-State)

Product data Supersedes data of 2000 Jun 19





18-bit GTL/GTL+ to LVTTL/TTL bidirectional universal translator (3-State)

GTL16612

FEATURES

- 18-bit bidirectional bus interface
- Translates between GTL/GTL+ logic levels (B ports) and LVTTL/TTL logic levels (A ports)
- 5 V I/O tolerant on the LVTTL/TTL side (A ports)
- No bus current loading when LVTTL/TTL output is tied to 5 V bus
- 3-State buffers
- Output capability: +64 mA/-32 mA on the LVTTL/TTL side (A ports); +40 mA on the GTL/GTL+ side (B ports)
- TTL input levels on control pins
- Power-up reset
- Power-up 3-State
- Positive edge triggered clock inputs
- Latch-up protection exceeds 500 mA per JESD78
- ESD protection exceeds 2000 V HBM per JESD22-A114, 200 V MM per JESD22-A115 and 1000 V CDM per JESD22-C101

DESCRIPTION

The GTL16612 is a high-performance BiCMOS product designed for V_{CC} operation at 3.3 V with I/O compatibility up to 5 V.

This device is an 18-bit universal transceiver featuring non-inverting 3-State bus compatible outputs in both send and receive directions. Data flow in each direction is controlled by output enable (OEAB and OEBA), latch enable (LEAB and LEBA), and clock (CPAB and CPBA) inputs. For A-to-B data flow, the device operates in the transparent mode when LEAB is High. When LEAB is Low, the A data is latched if CPAB is held at a High or Low logic level. If LEAB is Low, the A-bus data is stored in the latch/flip-flop on the Low-to-High transition of CPAB. When OEAB is Low, the outputs are active. When OEAB is High, the outputs are in the high-impedance state. The clocks can be controlled with the clock-enable inputs (CEBA/CEAB).

Data flow for B-to-A is similar to that of A-to-B but uses OEBA, LEBA and CPBA.

QUICK REFERENCE DATA

OVERDO	2424455	CONDITIONS	TYPICAL	
SYMBOL	PARAMETER	T _{amb} = 25 °C	3.3 V	UNIT
t _{PLH} t _{PHL}	Propagation delay An to Bn or Bn to An	C _L = 50 pF	1.9	ns
C _{IN}	Input capacitance (Control pins)	V _I = 0 V or V _{CC}	4	pF
C _{I/O}	I/O pin capacitance	Outputs disabled; $V_{I/O} = 0 \text{ V or } V_{CC}$	8	pF
I _{CCZ}	Total supply current	Outputs disabled	12	mA

ORDERING INFORMATION

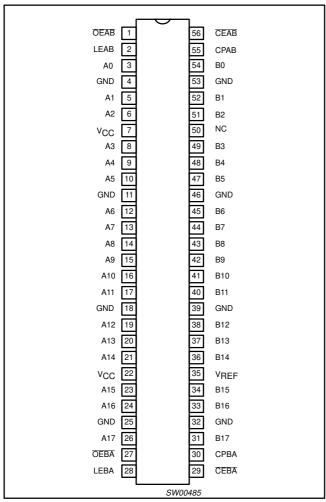
PACKAGES	TEMPERATURE RANGE	ORDER CODE	DWG NUMBER
56-Pin Plastic SSOP	-40 to +85 °C	GTL16612DL	SOT371-1
56-Pin Plastic TSSOP	-40 to +85 °C	GTL16612DGG	SOT364-1

Standard packing quantities and other packaging data is available at www.philipslogic.com/packaging.

18-bit GTL/GTL+ to LVTTL/TTL bidirectional universal translator (3-State)

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PIN CONFIGURATION



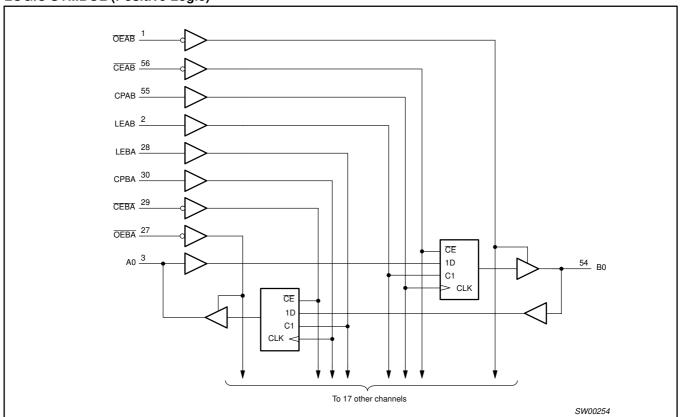
PIN DESCRIPTION

PIN NUMBER	SYMBOL	NAME AND FUNCTION
1, 27	OEAB/OEBA	A-to-B/ B-to-A Output enable input (active Low)
29, 56	CEBA/CEAB	B-to-A/A-to-B clock enable
2, 28	LEAB/LEBA	A-to-B/B-to-A Latch enable input
55,30	CPAB/CPBA	A-to-B/B-to-A Clock input (active rising edge)
3, 5, 6, 8, 9, 10, 12, 13, 14, 15, 16, 17, 19, 20, 21, 23, 24, 26	A0-A17	Data inputs/outputs (A side)
54, 52, 51, 49, 48, 47, 45, 44, 43, 42, 41, 40, 38, 37, 36, 34, 33, 31	B0-B17	Data inputs/outputs (B side)
4, 11, 18, 25, 32, 39, 46, 53	GND	Ground (0 V)
7, 22	V _{CC}	Positive supply voltage
35	V_{REF}	GTL reference voltage
50	NC	No connection

18-bit GTL/GTL+ to LVTTL/TTL bidirectional universal translator (3-State)

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LOGIC SYMBOL (Positive Logic)



FUNCTION TABLE

	INPUTS						
CEAB1	EAB ¹ OEAB ¹ LEAB ¹ CPAB ¹ A						
Х	Н	Х	Х	Х	Z		
Х	L	Н	Х	L	L		
Х	L	Н	Х	Н	Н		
Н	L	L	Х	Χ	B _O ²		
Н	L	L	Х	Х	B _O ²		
L	L	L	↑	L	L		
L	L	L	1	Н	Н		
L	L	L	Н	Х	B_O^2		
L	L	L	L	Χ	B_O^3		

- X = Don't care
- H = High voltage level
- L = Low voltage level
- ↑ = Low to High
- Z = High impedance "off" state
- 1. A-to-B data flow is shown: B-to-A flow is similar but uses OEBA, LEBA, CPBA, and CEBA.
- 2. Output level before the indicated steady-state input conditions were established.
- 3. Output level before the indicated steady-state input conditions were established, provided that CPAB was Low before LEAB went Low.

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ABSOLUTE MAXIMUM RATINGS 1, 2

SYMBOL	PARAMETER	CONDITIONS	RATING	UNIT
V _{CC}	DC supply voltage		-0.5 to +4.6	V
I _{IK}	DC input diode current	V ₁ < 0	-50	mA
V	DC innutualisma3	A port	-0.5 to +7.0	V
VI	DC input voltage ³	B port	-0.5 to +4.6	V
l _{ok}	DC output diode current	V _O < 0; A port	-50	mA
V	DC subsub units and	Output in Off or High state; A port	-0.5 to +7.0	V
Vo	DC output voltage ³	Output in Off or High state; B port	-0.5 to +4.6	V
1	Comment into any output in the LOW state	A port	128	mA
l _{OL}	Current into any output in the LOW state	B port	80	mA
I _{OH}	Current into any output in the HIGH state	A port	-64	mA
T _{stg}	Storage temperature range		-65 to +150	°C

NOTES:

RECOMMENDED OPERATING CONDITIONS

CVMDOL	DADAMETED	TECT CONDITIONS	3.3 V RAN	IGE LIMITS	шит
SYMBOL	PARAMETER	TEST CONDITIONS	MIN	MAX	UNIT
V _{CC}	DC supply voltage		3.0	3.6	V
M	Taurainatian valtana	GTL	1.14	1.26	V
V_{TT}	Termination voltage	GTL+	1.35	1.65	V
V	CTI reference veltere	GTL	0.74	0.87	V
V_{REF}	GTL reference voltage	GTL+	0.9	1.10	7 °
M	Input voltage	B port	0	V _{TT}	V
VI		Except B port	Except B port	0	5.5
V	LUCII level innet velte e e	B port	V _{REF} +50 mV		V
V _{IH}	HIGH-level input voltage Except B port		2.0		7 °
W	LOWIssalisastuskass	B port		V _{REF} -50 mV	V
V_{IL}	LOW-level input voltage	Except A port		0.8	7 °
I _{OH}	HIGH-level output current	A port		-32	mA
	LOW level output ourrent	B port		40	A
l _{OL}	LOW-level output current	A port		64	- mA
T _{amb}	Operating free-air temperature range		-40	+85	°C

^{1.} Stresses beyond those listed may cause permanent damage to the device. These are stress ratings only and functional operation of the device at these or any other conditions beyond those indicated under "recommended operating conditions" is not implied. Exposure to absolute-maximum-rated conditions for extended periods may affect device reliability.

The performance capability of a high-performance integrated circuit in conjunction with its thermal environment can create junction

temperatures which are detrimental to reliability. The maximum junction temperature of this integrated circuit should not exceed 150°C.

^{3.} The input and output negative voltage ratings may be exceeded if the input and output clamp current ratings are observed.

18-bit GTL/GTL+ to LVTTL/TTL bidirectional universal translator (3-State)

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DC ELECTRICAL CHARACTERISTICS (3.3 V \pm 0.3 V RANGE)

						LIMITS				
SYMBOL	PARAMETER TEST CONDITIONS				PARAMETER TEST CONDITIONS		Temp =	-40 to +	85 °C	UNIT
					MIN	TYP ¹	MAX			
V _{IK}	Input clamp vo	Itage	V _{CC} = 3.0 V; I _{IK} = -18 mA			-0.85	-1.2	V		
.,			$V_{CC} = 3.0 \text{ to } 3.6 \text{ V}; I_{OH} = -100 \mu\text{A}$		V _{CC} -0.2	V_{CC}				
V _{OH}	High-level outp	out voitage	V _{CC} = 3.0 V; I _{OH} = -32 mA	- A port	2.0	2.3		V		
			$V_{CC} = 3.0 \text{ V}; I_{OL} = 100 \mu\text{A}$			0.07	0.2			
			V _{CC} = 3.0 V; I _{OL} = 16 mA	A		0.25	0.4	V		
V_{OL}	Low-level outp	ut voltage	V _{CC} = 3.0 V; I _{OL} = 32 mA	- A port		0.3	0.5	V		
			V _{CC} = 3.0 V; I _{OL} = 64 mA			0.4	0.55			
			V _{CC} = 3.0 V; I _{OL} = 40 mA	B port		0.4	0.5	V		
			$V_{CC} = 3.6 \text{ V}; V_I = V_{CC} \text{ or GND}$	O a material relieva		0.1	±1	_		
			V _{CC} = 0 or 3.6 V; V _I = 5.5 V	= 5.5 V Control pins		0.1	10	μΑ		
			V _{CC} = 3.6 V; V _I = 5.5 V			0.1	20	μΑ		
l _l	Input leakage of	current	V _{CC} = 3.6 V; V _I = V _{CC}	I/O Data pins ⁴ A port		0.5	10			
			V _{CC} = 3.6 V; V _I = 0	A port		0.1	-5			
			$V_{CC} = 3.6 \text{ V}; V_I = V_{TT} \text{ or GND}$	B port			±5	μΑ		
l _{OFF}	Output off curre	ent	$V_{CC} = 0 \text{ V}; V_{I} \text{ or } V_{O} = 0 \text{ to } 4.5 \text{ V}$			0.1	±100	μΑ		
	Des Held some		V _{CC} = 3 V; V _I = 0.8 V		75	130		_		
I _{HOLD}	Bus Hold curre	ent, A outputs	V _{CC} = 3 V; V _I = 2.0 V		-75	-140		μΑ		
I _{EX}	Current into an High state whe	output in the n V _O > V _{CC}	V _O = 5.5 V; V _{CC} = 3.0 V	A port		10	125	μА		
I _{PU/PD}	Power up/dowi		$V_{CC} \le 1.2 \text{ V}; V_O = 0.5 \text{ V to } V_{CC}; V_O = 0.5 \text{ Don't care}$	I_{I} = GND or V_{CC}		1.0	±100	μА		
I _{CCH}			Outputs high			5.0	9.0			
I _{CCL}	A-Port		Outputs low			10.5	18.5			
I _{CCZ} 5		V _{CC} = 3.6 V	Disabled	$V_I = GND \text{ or } V_{CC}, I_O = 0$		6.0	11.5	mA		
I _{CCH}	D. David		Outputs high			9.7	17.5			
I _{CCL}	B-Port		Outputs low			7.0	12.0			
ΔI_{CC}	Additional supplingut pin ²	oly current per	V _{CC} = 3 V to 3.6 V; One input at V Other inputs at V _{CC} or GND	/ _{CC} -0.6 V,		0.04	0.2	mA		

- All typical values are at V_{CC} = 3.3 V and T_{amb} = 25 °C.
 This is the increase in supply current for each LVTTL input at the specified voltage level other than V_{CC} or GND
 This parameter is valid for any V_{CC} between 0 V and 1.2 V with a transition time of up to 10 msec. From V_{CC} = 1.2 V to V_{CC} = 3.3 V ± 0.3 V a transition time of 100 μ sec is permitted. This parameter is valid for $T_{amb} = 25$ °C only.
- 4. Unused pins at V_{CC} or GND.

 5. I_{CCZ} is measured with outputs pulled up to V_{CC} or pulled down to ground.

18-bit GTL/GTL+ to LVTTL/TTL bidirectional universal translator (3-State)

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AC CHARACTERISTICS (A PORT)

GND = 0 V; t_r = t_f = 2.5 ns; C_L = 50 pF; R_L = 500 Ω ; T_{amb} = -40 to +85 °C.

				GTL			GTL+		
	GTL16612 An Po	ort	Vcc	c = 3.3 V ±0.	.3 V	V_{CC} = 3.3 V ±0.3 V			
			,	V _{REF} = 0.8 V	/	,	/ _{REF} = 1.0 \	/	UNIT
SYMBOL	PARAMETER	WAVEFORM	MIN	TYP ¹	MAX	MIN	TYP ¹	MAX	
t _{PLH}	Bn to An	2	1.6	3.0	5.0	1.6	3.0	5.0	ns
t _{PHL}	Bn to An	2	3.0	4.9	6.3	3.0	4.9	6.3	ns
t _{PLH}	LEBA to An	3	1.6	2.7	4.2	1.6	2.7	4.2	ns
t _{PHL}	LEBA to An	3	1.6	2.8	4.3	1.6	2.8	4.3	ns
t _{PLH}	CPBA to An	1	1.9	3.4	4.7	1.9	3.4	4.7	ns
t _{PHL}	CPBA to An	1	1.8	3.8	5.2	1.8	3.8	5.2	ns
t _{PZH}	OEBA to An	5	1.5	2.6	4.2	1.5	2.6	4.2	ns
t _{PHZ}	OEBA to An	5	1.4	2.9	4.8	1.4	2.9	4.8	ns
t _{PZL}	OEBA to An	6	1.3	2.4	3.8	1.3	2.4	3.8	ns
t _{PLZ}	OEBA to An	6	1.2	2.2	3.5	1.2	2.2	3.5	ns

NOTE:

AC CHARACTERISTICS (B PORT)

GND = 0 V; t_r = t_f = 2.5 ns; C_L = 30 pF; R_L = 25 Ω ; T_{amb} = -40 to +85 °C.

				GTL			GTL+		
	GTL16612 Bn P	ort	V _C	V _{CC} = 3.3 V ±0.3 V			$V_{CC} = 3.3 \text{ V} \pm 0.3 \text{ V}$		
			,	V _{REF} = 0.8 \	/	,	/ _{REF} = 1.0 \	<i>'</i>	UNIT
SYMBOL	PARAMETER	WAVEFORM	MIN	TYP ¹	MAX	MIN	TYP ¹	MAX	
t _{PLH}	An to Bn	2	1.4	2.4	3.7	1.3	2.4	3.7	ns
t _{PHL}	An to Bn	2	1.3	2.5	4.0	1.4	2.6	4.2	ns
t _{PLH}	LEAB to Bn	3	1.7	3.0	4.4	1.8	3.0	4.6	ns
t _{PHL}	LEAB to Bn	3	2.1	3.5	5.4	2.3	3.6	5.5	ns
t _{PLH}	CPAB to Bn	1	1.8	3.1	4.5	1.9	3.1	4.8	ns
t _{PHL}	CPAB to Bn	1	2.3	3.6	5.4	2.4	3.8	5.8	ns
t _{PLH}	OEAB to Bn	7	1.1	2.1	3.3	1.4	2.0	3.5	ns
t _{PHL}	OEAB to Bn	7	1.6	2.8	4.4	1.0	2.9	4.5	ns

NOTE:

^{1.} Typical values are at V_{CC} = 3.3 V, T_{amb} = +25 °C.

^{1.} Typical values are at V_{CC} = 3.3 V, T_{amb} = +25 °C.

18-bit GTL/GTL+ to LVTTL/TTL bidirectional universal translator (3-State)

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AC SETUP REQUIREMENTS (3.3 V ± 0.3 V RANGE)

A Port: GND = 0 V; Input $t_r = t_f = 2.5 \text{ ns}$; $C_L = 50 \text{ pF}$; $R_L = 500 \Omega$; $T_{amb} = -40 \text{ to } +85 \text{ °C}$; $V_{REF} = 0.8 \text{ V or } 1.0 \text{ V}$. B Port: GND = 0 V; Input $t_r = t_f = 2.5 \text{ ns}$; $C_L = 30 \text{ pF}$; $R_L = 25 \Omega$; $V_{REF} = 0.8 \text{ V or } 1.0 \text{ V}$.

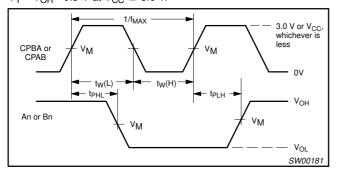
			LIN	UNIT	
SYMBOL	PARAMETER	WAVEFORM	$V_{CC} = 3.3 \text{ V} \pm 0.3 \text{ V}$		
			MIN	MAX	1
t _s (H)	Setup time, High or Low	4	1.5		ns
t _s (L)	Bn to CPBA	4	1.5		ns
t _s (H)	Setup time, High or Low	4	2.0		ns
t _s (L)	An to CPAB	4	3.0		ns
t _h (H)	Hold time, High or Low	4	1.0		ns
t _h (L)	Bn to CPBA, or An to CPAB	4	1.0		ns
t _s (H)	Setup time, High or Low	4	1.0		ns
t _s (L)	Bn to LEBA, or An to LEAB	4	1.0		ns
t _h (H)	Hold time, High or Low	4	1.5		ns
t _h (L)	Bn to LEBA, or An to LEAB	4	1.5		ns
t _s (H)	Setup time, High or Low	4	1.0		ns
t _s (L)	CEAB to CPAB, or CEBA to CPBA	4	1.0		ns
t _h (H)	Hold time, High or Low	4	1.5		ns
t _h (L)	CEAB to CPAB, or CEBA to CPBA	4	1.0		ns
t _w (H)	Pulse width, High or Low	4	2.0		ns
t _w (L)	CPBA or CPAB	4	2.0		ns
t _w (H)	Pulse width, High LEBA or LEAB	3	1.5		ns

18-bit GTL/GTL+ to LVTTL/TTL bidirectional universal translator (3-State)

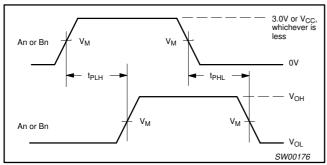
GTL16612

AC WAVEFORMS

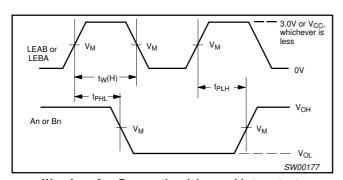
 V_M = 1.5 V at $V_{CC} \ge 3.0$ V. V_M = 1.5 V for A ports and control pins; V_M = 0.8 V for B ports in GTL mode; V_M = 1.0 V for B ports in GTL+ mode. $V_X = V_{OL} + 0.3$ V at $V_{CC} \ge 3.0$ V. $V_Y = V_{OH} - 0.3$ V at $V_{CC} \ge 3.0$ V.



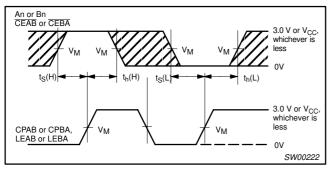
Waveform 1. Propagation delay, clock input to output, clock pulse width, and maximum clock frequency



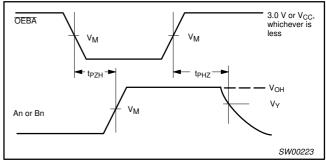
Waveform 2. Propagation delay, transparent mode



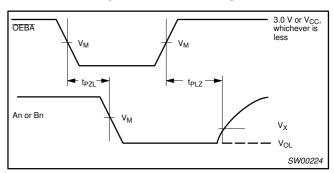
Waveform 3. Propagation delay, enable to output, and enable pulse width



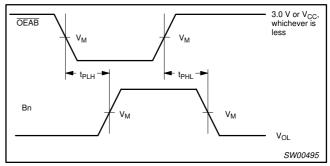
Waveform 4. Data setup and hold times



Waveform 5. 3-State output enable time to high level and output disable time from high level



Waveform 6. 3-State output enable time to low level and output disable time from low level

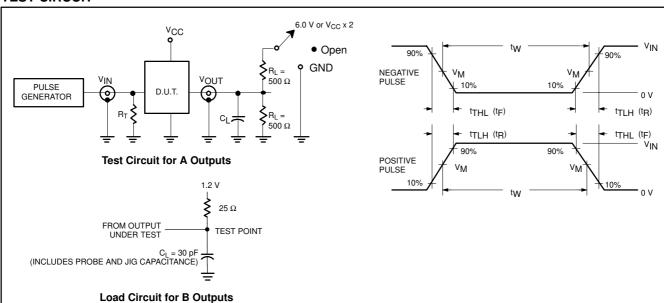


Waveform 7. Output enable time on open collector output with pullup

18-bit GTL/GTL+ to LVTTL/TTL bidirectional universal translator (3-State)

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TEST CIRCUIT



SWITCH POSITION

TEST	SWITCH
t _{PLZ} /t _{PZL}	6 V
t _{PLH} /t _{PHL}	Open
t _{PHZ} /t _{PZH}	GND

DEFINITIONS

 R_L = Load resistor; see AC CHARACTERISTICS for value.

C_L = Load capacitance includes jig and probe capacitance: See AC CHARACTERISTICS for value.

 R_T = Termination resistance should be equal to Z_{OUT} of pulse generators.

	INPUT PULSE REQUIREMENTS							
FAMILY	Amplitude	Rep. Rate	t _W	t _R	t _F			
74GTL16	3.0 V or V _{CC} whichever is less	≤10 MHz	500 ns	≤2.5 ns	≤2.5 ns			

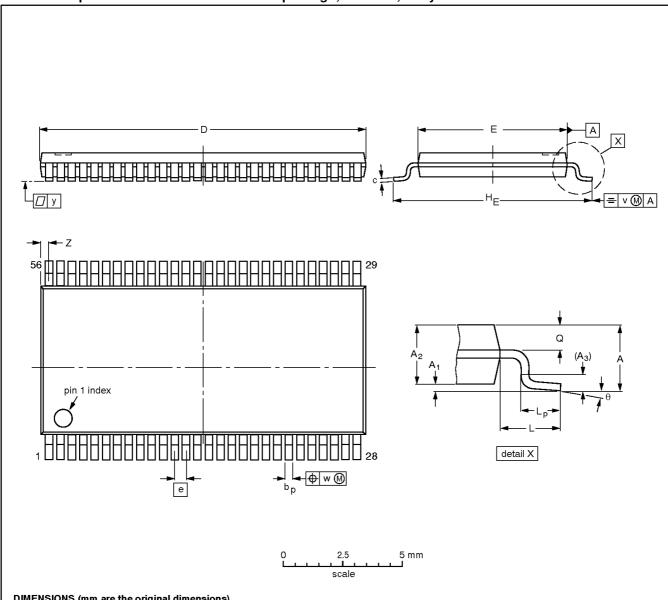
SW00255

18-bit GTL/GTL+ to LVTTL/TTL bidirectional universal translator (3-State)

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TSSOP56: plastic thin shrink small outline package; 56 leads; body width 6.1mm

SOT364-1



DIMENSIONS (mm are the original dimensions).

UNIT	A max.	A ₁	A ₂	А3	bp	С	D ⁽¹⁾	E ⁽²⁾	е	HE	L	Lp	Q	>	w	у	z	θ
mm	1.2	0.15 0.05	1.05 0.85	0.25	0.28 0.17	0.2 0.1	14.1 13.9	6.2 6.0	0.5	8.3 7.9	1.0	0.8 0.4	0.50 0.35	0.25	0.08	0.1	0.5 0.1	8° 0°

- 1. Plastic or metal protrusions of 0.15 mm maximum per side are not included.
- 2. Plastic interlead protrusions of 0.25 mm maximum per side are not included.

OUTLINE		REFER	EUROPEAN	ISSUE DATE			
VERSION	IEC	JEDEC	EIAJ		PROJECTION	ISSUE DATE	
SOT364-1		MO-153EE				-93-02-03 95-02-10	

18-bit GTL/GTL+ to LVTTL/TTL bidirectional universal translator (3-State)

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REVISION HISTORY

Rev	Date	Description
_4	20021213	Product data (9397 750 10862); ECN 853-2166 29245 of 03 December 2002
		Modifications:
		New package release.
_3	20000619	Product data (9397 750 07217); ECN 853-2166 23903 of 19 June 2000.

18-bit GTL/GTL+ to LVTTL/TTL bidirectional universal translator (3-State)

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Data sheet status

Level	Data sheet status ^[1]	Product status ^{[2] [3]}	Definitions
1	Objective data	Development	This data sheet contains data from the objective specification for product development. Philips Semiconductors reserves the right to change the specification in any manner without notice.
II	Preliminary data	Qualification	This data sheet contains data from the preliminary specification. Supplementary data will be published at a later date. Philips Semiconductors reserves the right to change the specification without notice, in order to improve the design and supply the best possible product.
III	Product data	Production	This data sheet contains data from the product specification. Philips Semiconductors reserves the right to make changes at any time in order to improve the design, manufacturing and supply. Relevant changes will be communicated via a Customer Product/Process Change Notification (CPCN).

- [1] Please consult the most recently issued data sheet before initiating or completing a design.
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